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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/623,861	07/21/2003	Tyler A. Lowrey	ITO.0513C1US (P13341C) 6409		
7:	590 12/28/2004		EXAMINER		
Trop, Pruner & Hu, P.C.			SCHILLINGER, LAURA M		
Suite 100			Approprie	DARED MILITER	
8554 Katy Freeway			ART UNIT	PAPER NUMBER	
Houston, TX 77024			2813		

DATE MAILED: 12/28/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

•	Applic	cation No.	Applicant(s)				
Office Action Summe	10/623	3,861	LOWREY, TYLER	Α.			
Office Action Summa	Exami	ner	Art Unit				
\		M. Schillinger	2813				
The MAILING DATE of this collection for Reply	mmunication appears on	the cover sheet wit	th the correspondence add	iress			
A SHORTENED STATUTORY PERITHE MAILING DATE OF THIS COM Extensions of time may be available under the prafter SIX (6) MONTHS from the mailing date of the lifthe period for reply specified above is less than If NO period for reply is specified above, the max Failure to reply within the set or extended period Any reply received by the Office later than three rearned patent term adjustment. See 37 CFR 1.7	MUNICATION. ovisions of 37 CFR 1.136(a). In no is communication. thirty (30) days, a reply within the mum statutory period will apply an for reply will, by statute, cause the nonths after the mailing date of thi	o event, however, may a re statutory minimum of thirty nd will expire SIX (6) MON1 application to become AB/	eply be timely filed (30) days will be considered timely. THS from the mailing date of this con ANDONED (35 U.S.C. § 133).				
Status							
1) Responsive to communication	(s) filed on 13 Decembe	er 2004.					
2a) This action is FINAL.	2b)⊠ This action i		•				
3)☐ Since this application is in con							
closed in accordance with the	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims							
4) ⊠ Claim(s) <u>1-50</u> is/are pending in 4a) Of the above claim(s) <u>11-3</u> 5) □ Claim(s) is/are allowed. 6) ⊠ Claim(s) <u>1-10 and 31-36</u> is/are 7) □ Claim(s) is/are objected. 8) □ Claim(s) are subject to	0 and 37-50 is/are withd rejected. I to.		ration.				
Application Papers							
9) The specification is objected to 10) The drawing(s) filed on Applicant may not request that an Replacement drawing sheet(s) in 11) The oath or declaration is objective.	is/are: a) accepted on a community objection to the drawing (cluding the correction is reco	(s) be held in abeyan quired if the drawing(ce. See 37 CFR 1.85(a). s) is objected to. See 37 CF				
Priority under 35 U.S.C. § 119							
12) Acknowledgment is made of a a) All b) Some * c) None 1. Certified copies of the p 2. Certified copies of the p	e of: riority documents have l riority documents have l opies of the priority docu rnational Bureau (PCT	been received. been received in A uments have been Rule 17.2(a)).	pplication No received in this National s	Stage			
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Re 3) Information Disclosure Statement(s) (PTO-Paper No(s)/Mail Date		Paper No(s	summary (PTO-413) s)/Mail Date nformal Patent Application (PTO)-152)			

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DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1-10 and 34-36 are rejected under 35 U.S.C. 102(e) as being anticipated by Harshfield ('156).

Harshfield teaches the following claimed limitations as cited below:

1 (Previously Presented). A method comprising:

forming a lower electrode (Fig. 18 (106));

covering the lower electrode with a protective layer such that said protective layer is

formed directly over said lower electrode (Fig. 18 (110)); and

forming a phase change material over said lower electrode (Fig.20 (118)- see Col.s 12-13,

lines: 65-5; see also Col.13-14, lines: 60-25).

2 (Original). The method of claim 1 further comprising:

defining a singulated opening (Fig. 19 (114));

forming a cup-shaped phase change material in said opening (Fig.20 (118)); and

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forming a thermally insulating material in the cup-shaped phase change material (Fig. 21 (122)).

- 3 (Original). The method of claim 2 including defining said phase change material using a planarization process (Fig. 22 and Col. 13, lines: 20-40).
- 4 (Original). The method of claim 3 including defining said phase change material using a chemical mechanical planarization technique(Fig. 22 and Col.13, lines:20-40).
- 5 (Original). The method of claim 2 including defining a sidewall spacer in said singulated opening (Fig. 37 (192))
- 6 (Original). The method of claim 5 including defining an electrode in said opening (Fig.21 (118)- annular electrode).
- 7 (Original). The method of claim 6 including using said sidewall spacer to define the cup-shape of said phase change material (Fig. 37 (192)).
- 8 (Original). The method of claim 6 including forming a base layer over a substrate and forming said lower electrode over said base layer(Col.12, lines: 15-20).
- 9. The method of claim 1 including sequentially forming said lower electrode (106)and then said protective layer (110) (Fig. 18).

10 (Original). The method of claim 9 including etching said lower electrode and said protective film using the same mask (Col.12, lines: 50-60).

34 (Previously Presented). The method of claim 1 including forming the protective layer of an insulator (Col.12, lines: 35-45).

35 (Previously Presented). The method of claim 34 including forming the protective layer of a material in the form of silicon nitride (Col.12, lines: 35-45).

36 (Previously Presented). The method of claim 35 including forming the silicon nitride in the form of Si3 N4 (Col.12, lines: 35-45).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 31-33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Harshfield as applied to claim 1 above, and further in view of Urabe ('302).

Harshfield teaches the limitations of claim 1 and teaches that both the lower electrode and protective layer can be formed by CVD, however fails expressly teach that both layers

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are formed in the same deposition chamber as recited by claims 31 and 32. Harshfield also fails to mention any chamber deposition process with regard to without venting back to atmosphere as recited by claim 33.

Urabe ('302) teaches a CVD method for depositing both titanium nitride and silicon nitride in the same chamber (Abs., lines: 1-10 and Fig.3). Furthermore, Urabe does not teach to vent back to atmosphere.

It would have been obvious to one of ordinary skill in the art to modify Harshfield's teachings to include forming both the lower electrode (made of titanium nitride) and the protective layer (made of silicon nitride) in the same chamber as taught by Urabe in order to reduce the number of processing steps which would be required in using two chambers. Moreover, Urabe fails to teach to back vent to atmosphere and therefore the Examiner understands that Urabe's chamber deposition is conducted without venting back to atmosphere.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Laura M. Schillinger whose telephone number is (571) 272-1697. The examiner can normally be reached on M-T, R-F 7:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W. Whitehead, Jr. can be reached on (571) 272-1702. The fax phone

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number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

LMS

12/24/04